



**SHTR30100CT, SHTRF30100CT,
SHTRI30100CT, SHTRB30100CT**

Low VF=0.57V at IF=7.5A

SCHOTTKY BARRIER RECTIFIERS		REVERSE VOLTAGE FORWARD CURRENT	100 30	Volts Amperes
FEATURES		TO-220AB	ITO-220AB	
<ul style="list-style-type: none"> Metal of silicon rectifier , majority carrier conduction Trench Schottky Technology Low power loss, high efficiency High current capability, low VF High surge capacity Plastic package has UL flammability classification 94V-0 For use in low voltage,high frequency inverters,free wheeling,switching power supplies, DC-DC converter,and polarity protection applications 				
		SHTR30100CT	SHTRF30100CT	
MECHANICAL DATA		TO-263AB	TO-262AA	
<ul style="list-style-type: none"> Case: TO-220AB / ITO-220AB / TO-262AA / TO-263AB Polarity: As marked on the body Weight: 0.08ounces,2.24 grams Mounting position :Any 				
		SHTRB30100CT	SHTRI30100CT	

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25°C ambient temperature unless otherwise specified.

Single phase, half wave ,60Hz, resistive or inductive load.

For capacitive load, derate current by 20%

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

CHARACTERISTICS	SYMBOL	SHTR30100CT, SHTRF30100CT, SHTRI30100CT, SHTRB30100CT		UNIT
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	100		V
Maximum RMS Voltage	V _{RMS}	70		V
Maximum DC Blocking Voltage	V _{DC}	100		V
Maximum Average Forward Rectified Current (See Fig.1)	I _(AV)	30		A
Maximum Average Forward Rectified Current (Per Leg)		15		
Peak Forward Surge Current 8.3ms Single Half Sine-Wave Super Imposed on Rated Load	I _{FSM}	150		A
Peak repetitive reverse current at $t_p = 2 \mu\text{s}$, 1 kHz	I _{RRM}	1		A
Operating Temperature Range	T _J	-55 to +150		°C
Storage Temperature Range	T _{STG}	-55 to +175		°C

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

PARAMETER / CONDITIONS	SYMBOL	Typ	Max	UNIT
Breakdown voltage per diode	V _{BR}	110 (minimun)	-	V
Instantaneous forward voltage per diode (Note1) IF=7.5A @TJ=25°C IF=7.5A @TJ=125°C IF=15A @TJ=25°C IF=15A @TJ=125°C	V _F	0.61 0.57 0.79 0.71	0.66 0.61 0.90 0.77	V
Maximum DC Reverse Current @TJ=25°C at Rated DC Bolcking Voltage @TJ=125°C	I _R	135 36		uA mA
Typical Junction Capacitance (Note2)	C _J	460		pF

THERMAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	Typ				UNIT
		SHTR30100CT	SHTRF30100CT	SHTRI30100CT	SHTRB30100CT	
Thermal Resistance Per Diode (Note3)	R _{θJC}	3.0	5.5	3.5	3.5	°C/W

NOTES:1.300us pulse width,2% duty cycle.

2.Measured at 1.0 MHz and applied reverse voltage of 5.0V DC.

3.Thermal resistance junction to case.

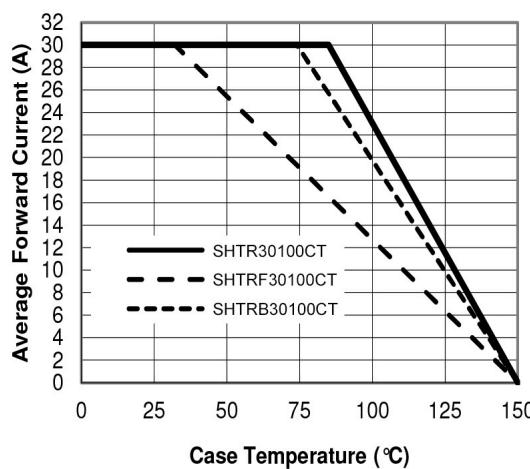


Figure 1. Forward Current Derating Curve

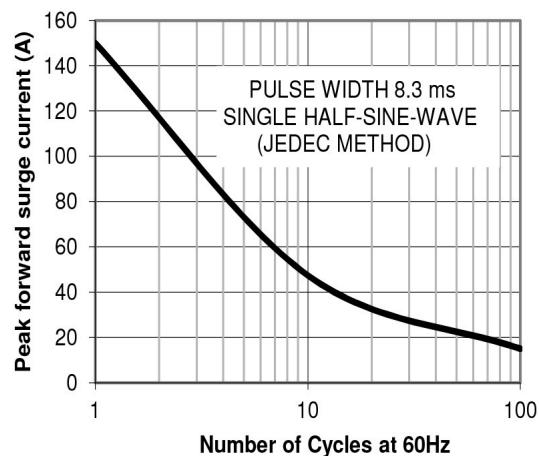


Figure 2. Maximum NON-Repetitive

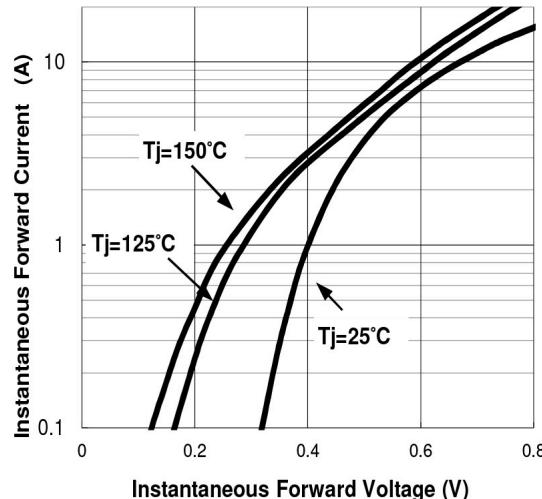


Figure 3. Typical Instantaneous Forward Characteristics Per Leg

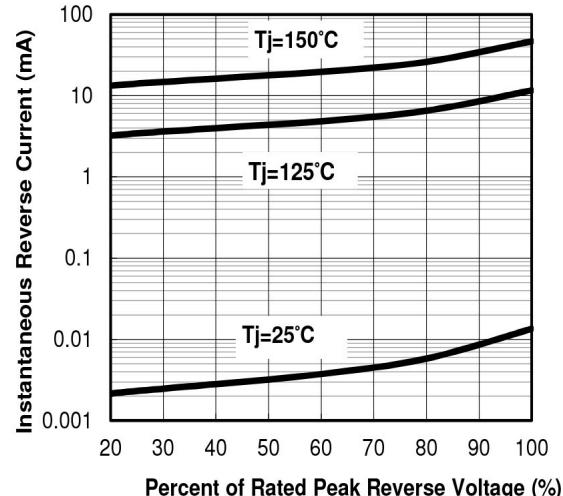


Figure 4. Typical Reverse Characteristics

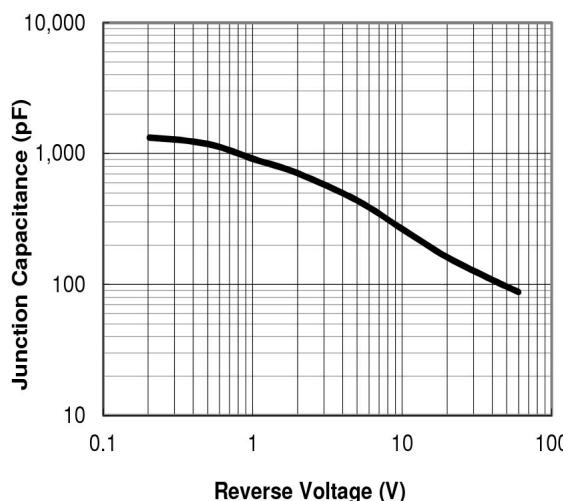


Figure 5. Typical Junction Capacitance

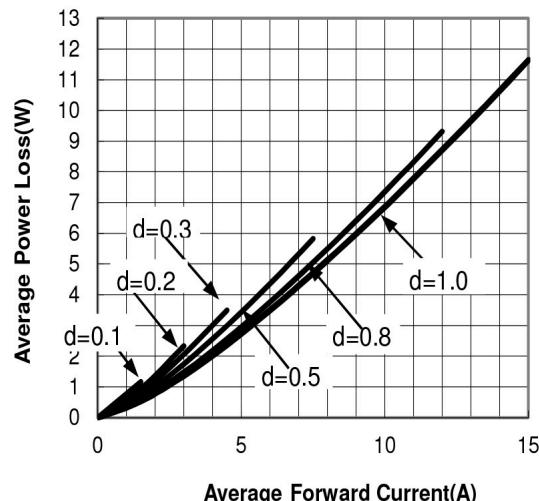
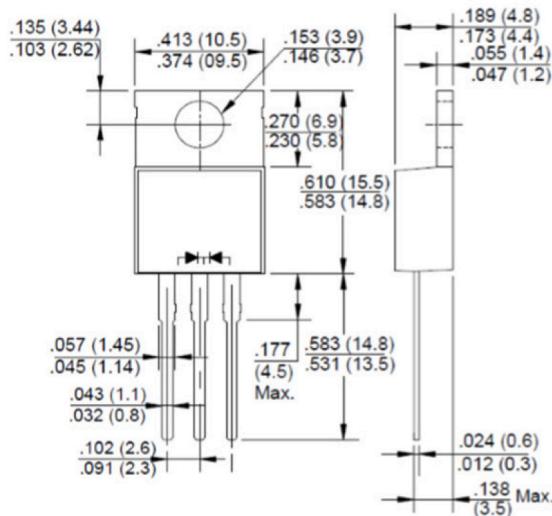
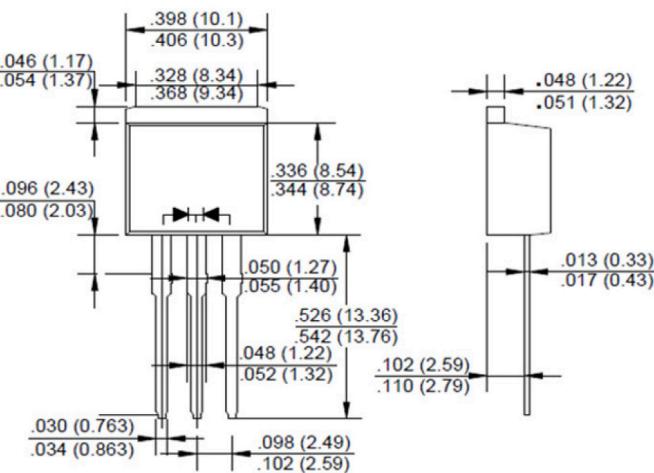


Figure 6. Forward Power Loss Characteristics

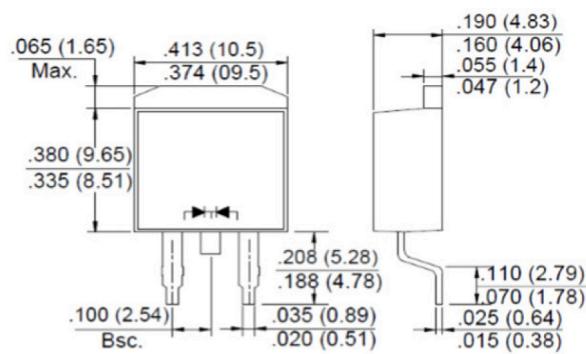
TO-220AB



TO-262AA



TO-263AB



ITO-220AB

